

Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

		Min.	Typ.	Max.
Collector-Emitter saturation voltage – Kollektor-Emitter-Sättigungsspg. ²⁾				
- I _C = 150 mA, - I _B = 15 mA	- V _{CEsat}	–	–	0.40 V
- I _C = 500 mA, - I _B = 50 mA	- V _{CEsat}	–	–	0.75 V
Base-Emitter saturation voltage – Basis-Emitter-Sättigungsspannung ²⁾				
- I _C = 150 mA, - I _B = 15 mA	- V _{BEsat}	0.75 V	–	0.95 V
- I _C = 500 mA, - I _B = 50 mA	- V _{BEsat}	–	–	1.3 V
Collector-Emitter cutoff current – Kollektor-Emitter-Reststrom				
- V _{CE} = 35 V, - V _{EB} = 0,4 V	- I _{CEX}	–	–	100 nA
Emitter-Base cutoff current – Emitter-Basis-Reststrom				
- V _{CE} = 35 V, - V _{EB} = 0,4 V	- I _{EBV}	–	–	100 nA
Gain-Bandwidth Product – Transitfrequenz				
- I _C = 20 mA, - V _{CE} = 10 V, f = 100 MHz	f _T	200 MHz	–	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität				
- V _{CB} = 5 V, I _E = i _e = 0, f = 1 MHz	C _{CBO}	–	–	8.5 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität				
- V _{EB} = 0.5 V, I _C = i _c = 0, f = 1 MHz	C _{EBO}	–	–	30 pf
Switching times – Schaltzeiten (between 10% and 90% levels)				
delay time	t _d	–	–	15 ns
rise time	t _r	–	–	20 ns
storage time	t _s	–	–	225 ns
fall time	t _f	–	–	30 ns
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft		R _{thA}	< 420 K/W ¹⁾	
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren		2N4401		

2 Tested with pulses t_p = 300 μs, duty cycle ≤ 2% – Gemessen mit Impulsen t_p = 300 μs, Schaltverhältnis ≤ 2%

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt-pad) an jedem Anschluss